

FIG. 1

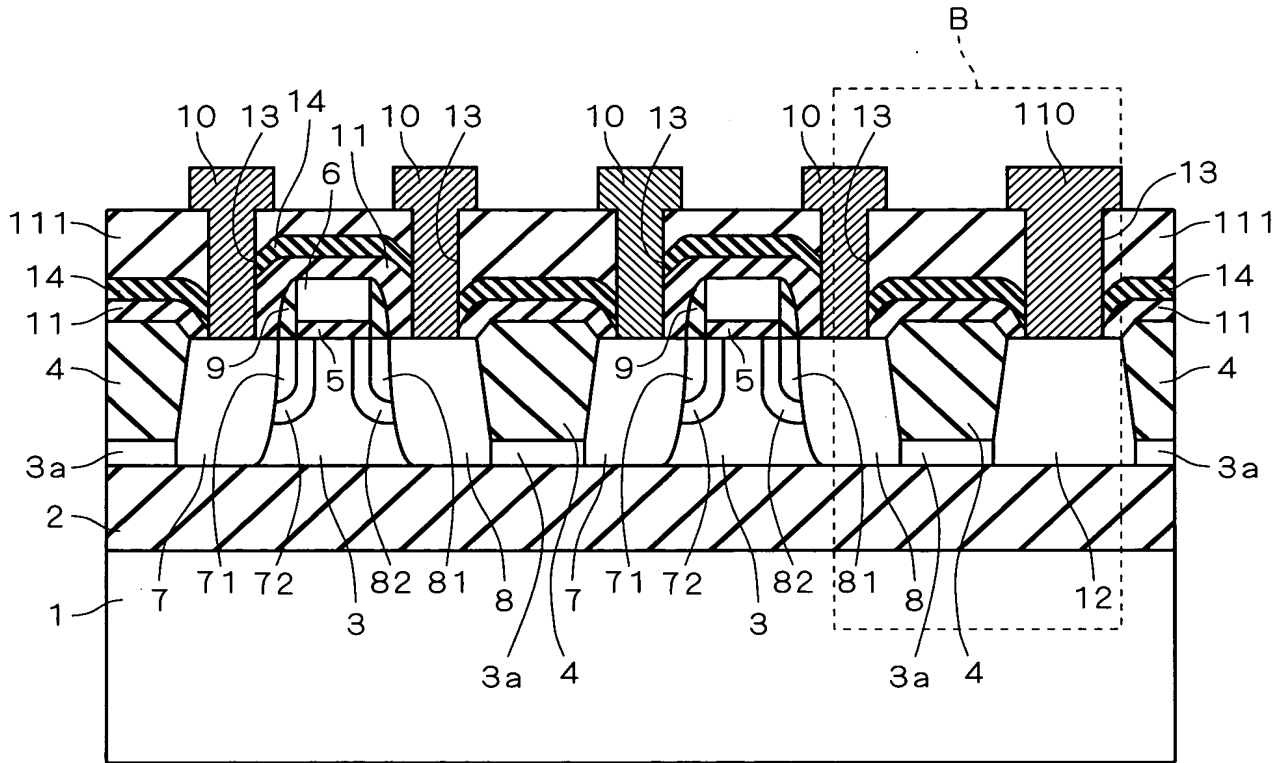
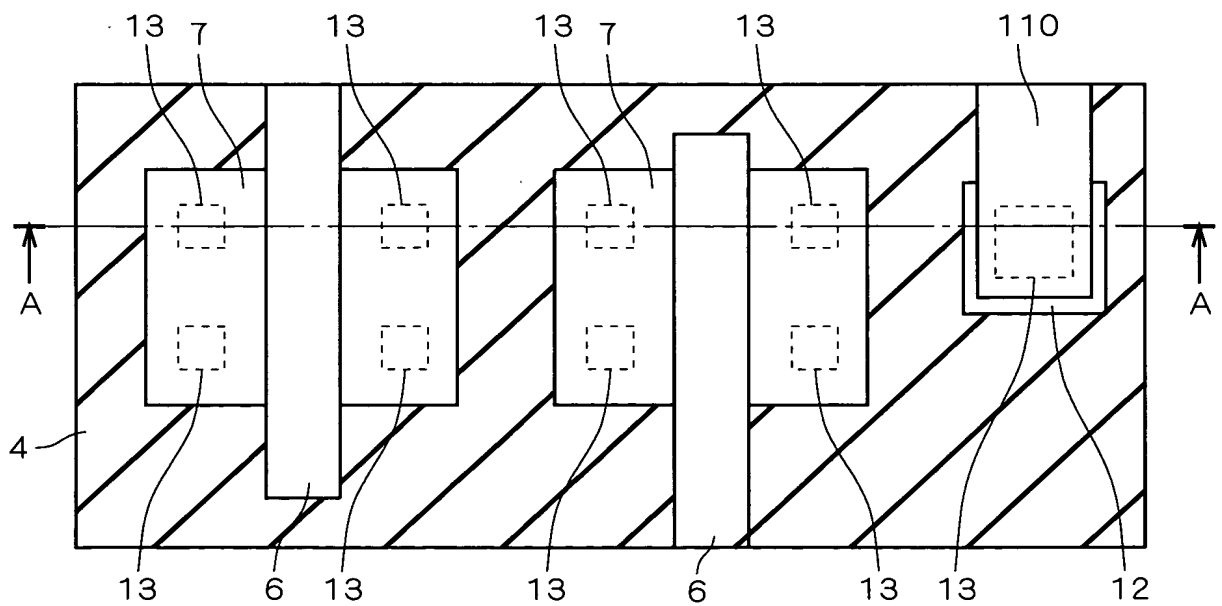
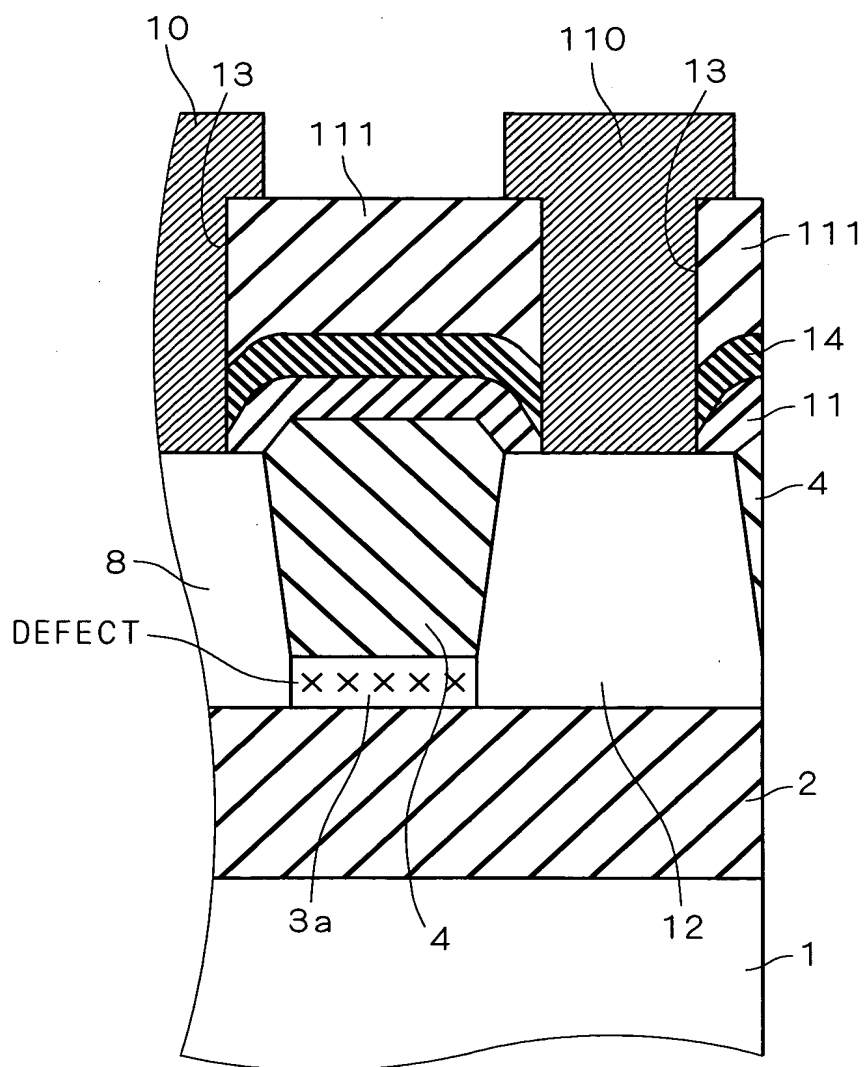


FIG. 2



F I G . 3



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[illegible]



FIG. 8

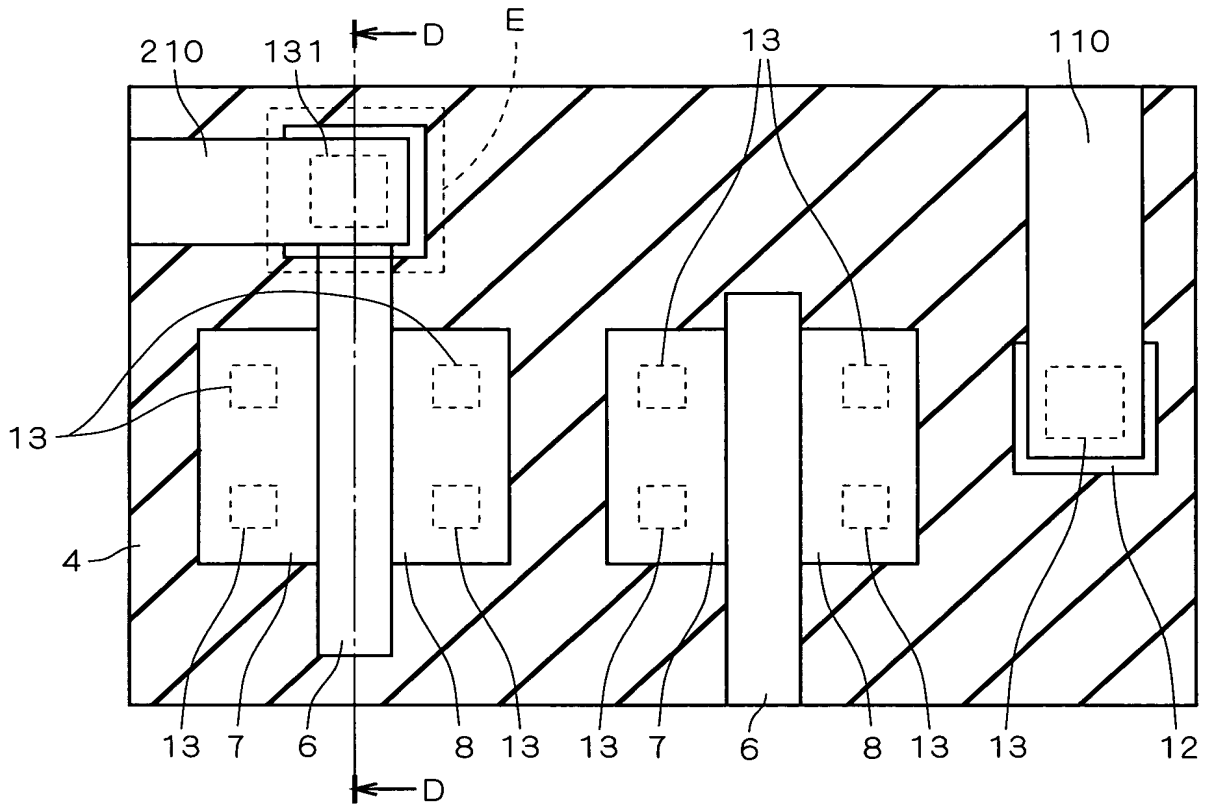


FIG. 9

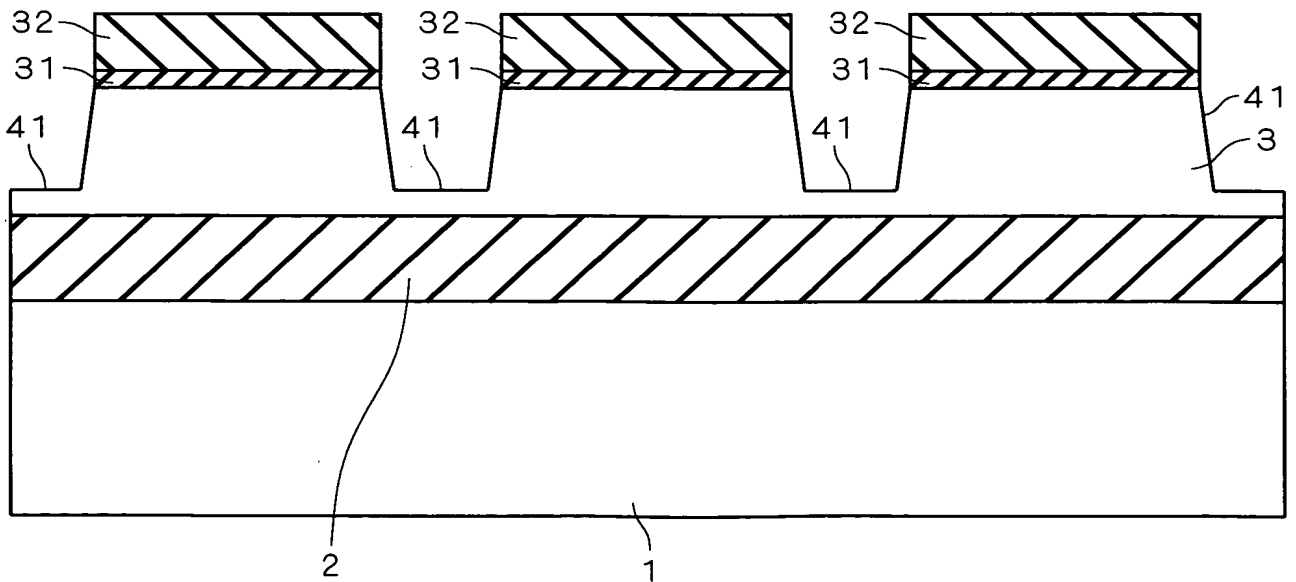


FIG. 10

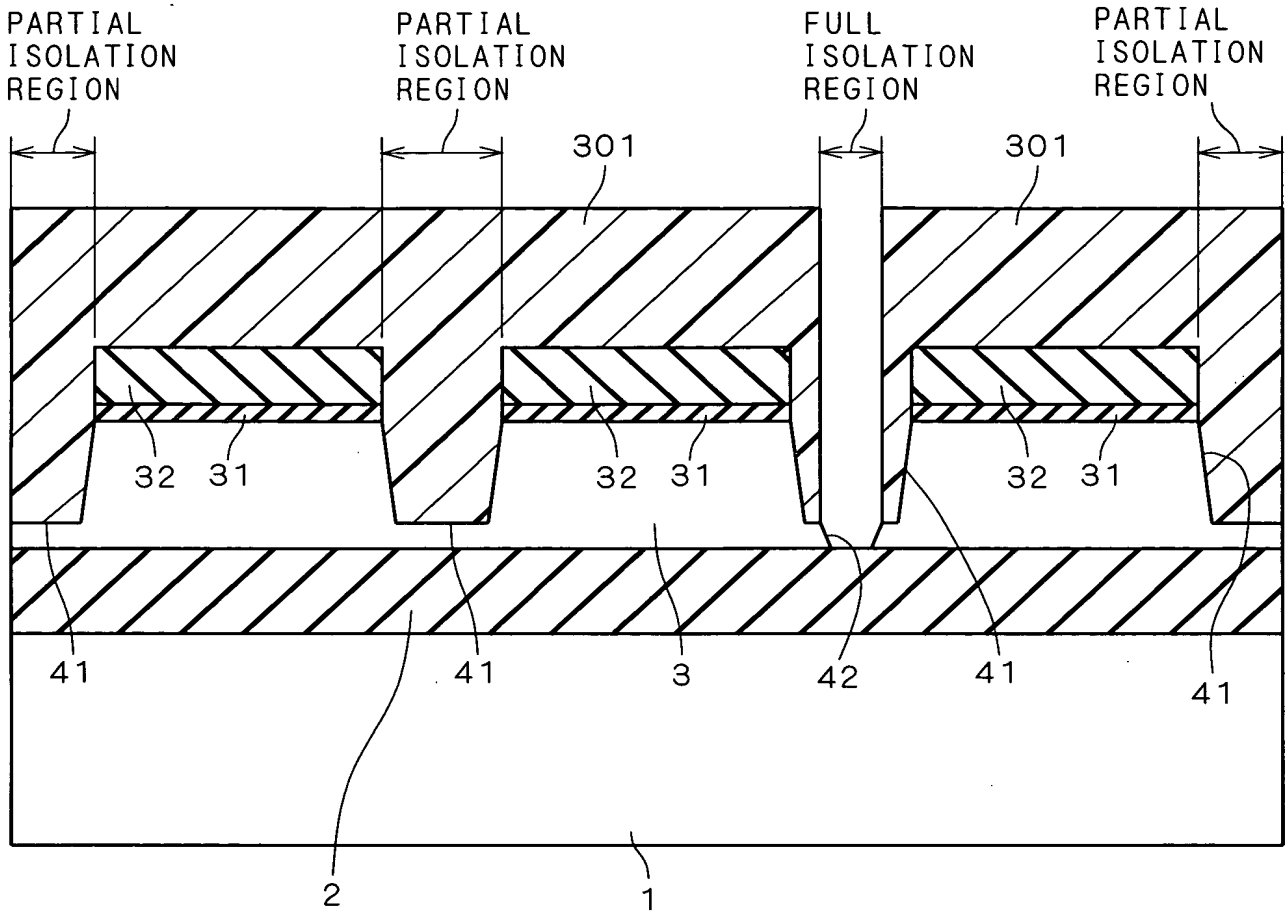


FIG. 11

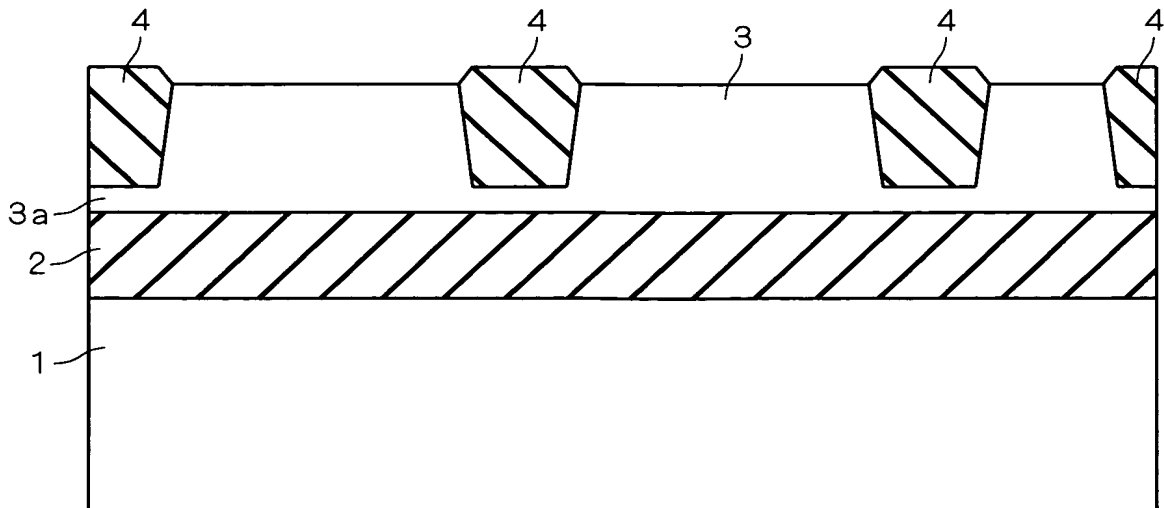


FIG. 12

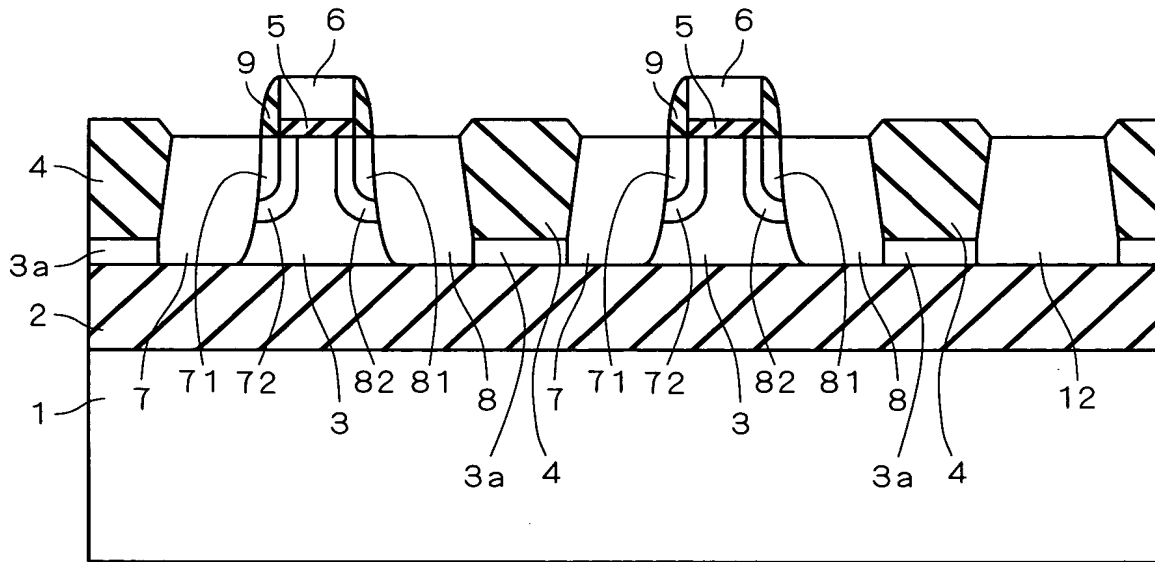
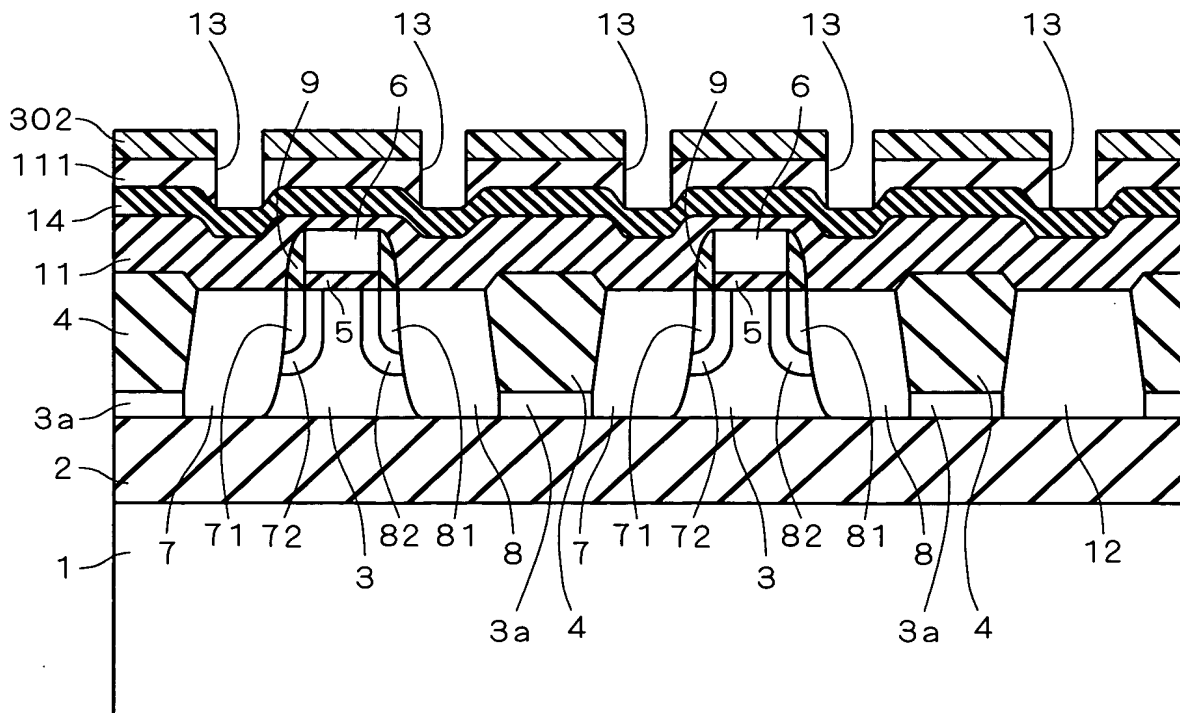


FIG. 13



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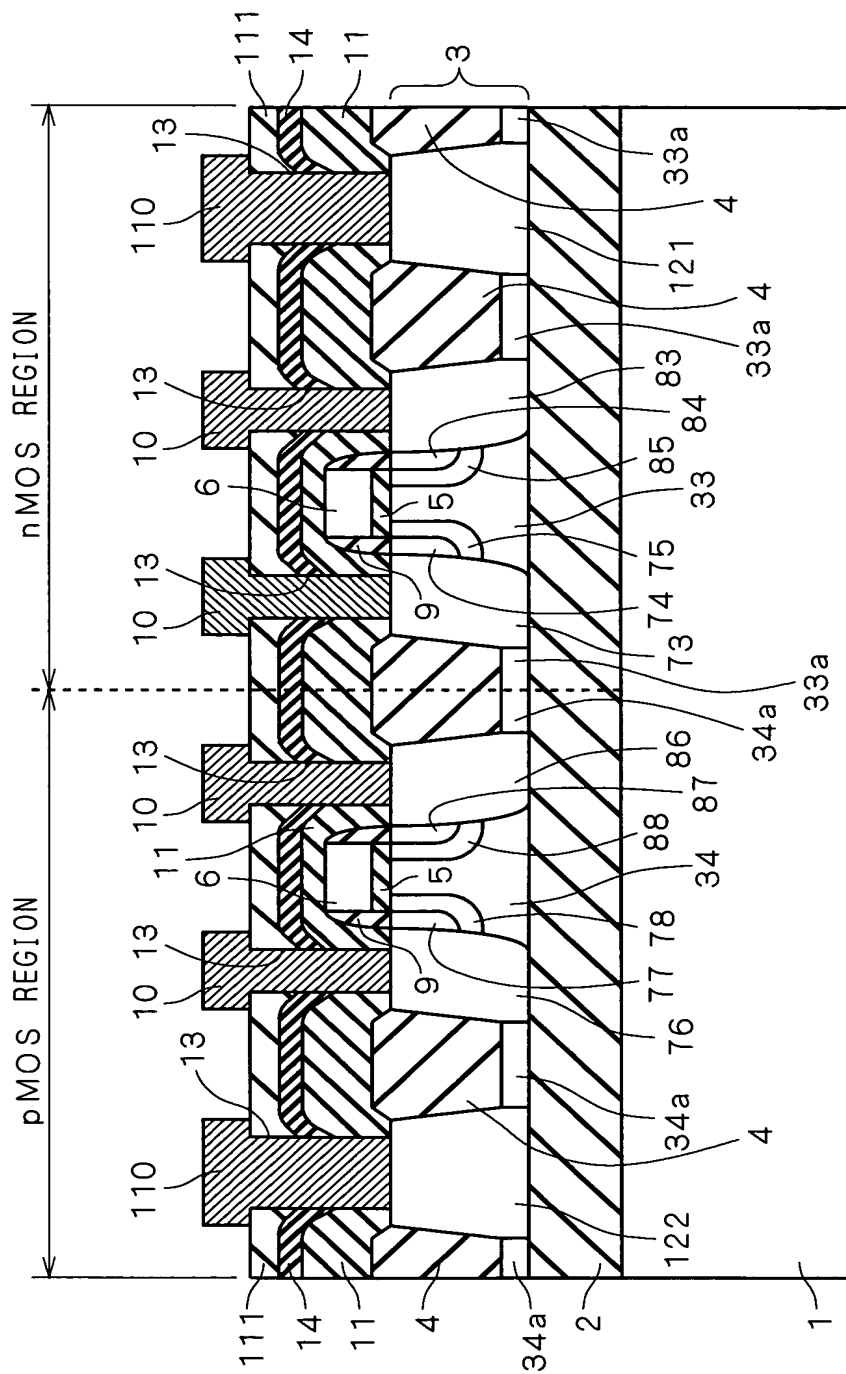


FIG. 14



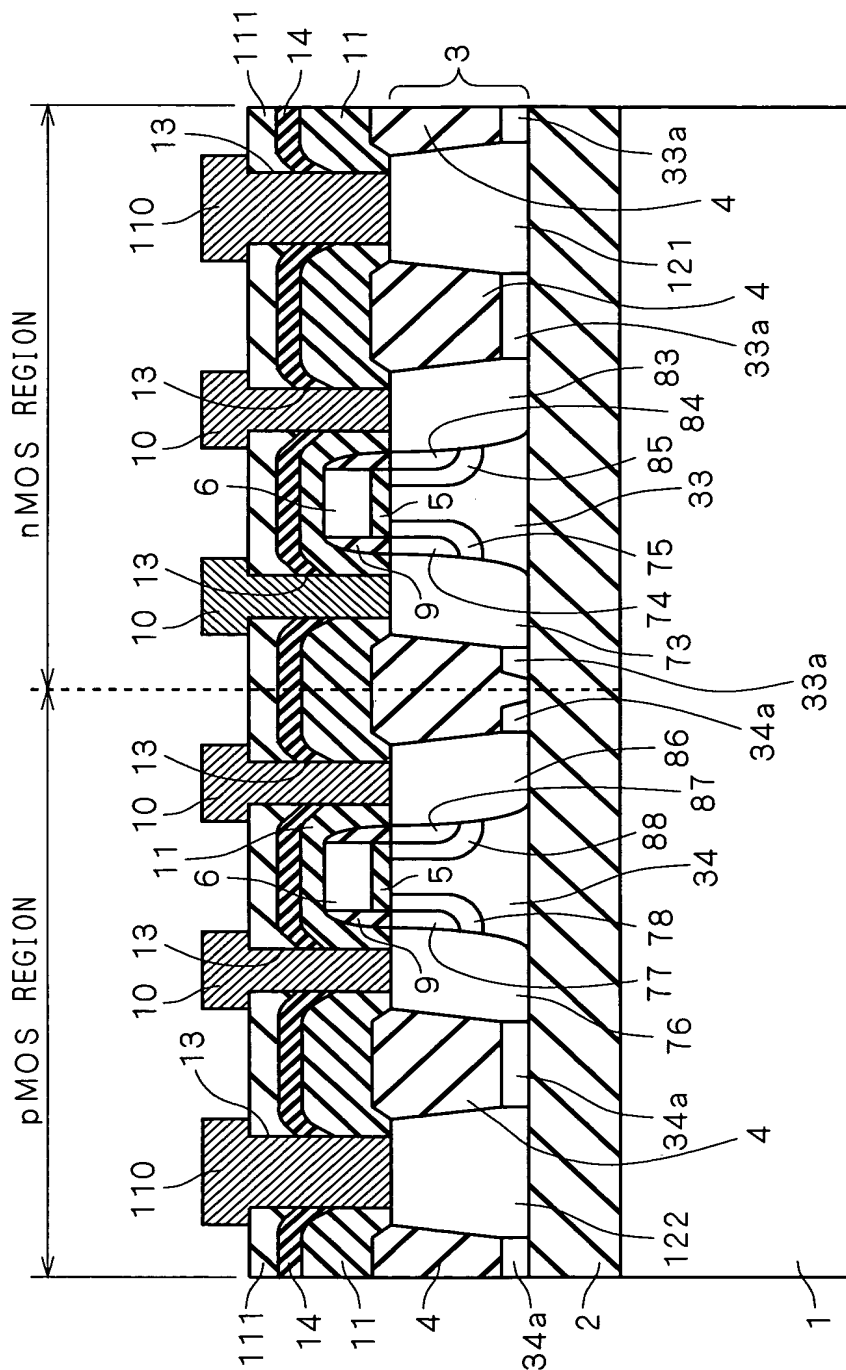


FIG. 15

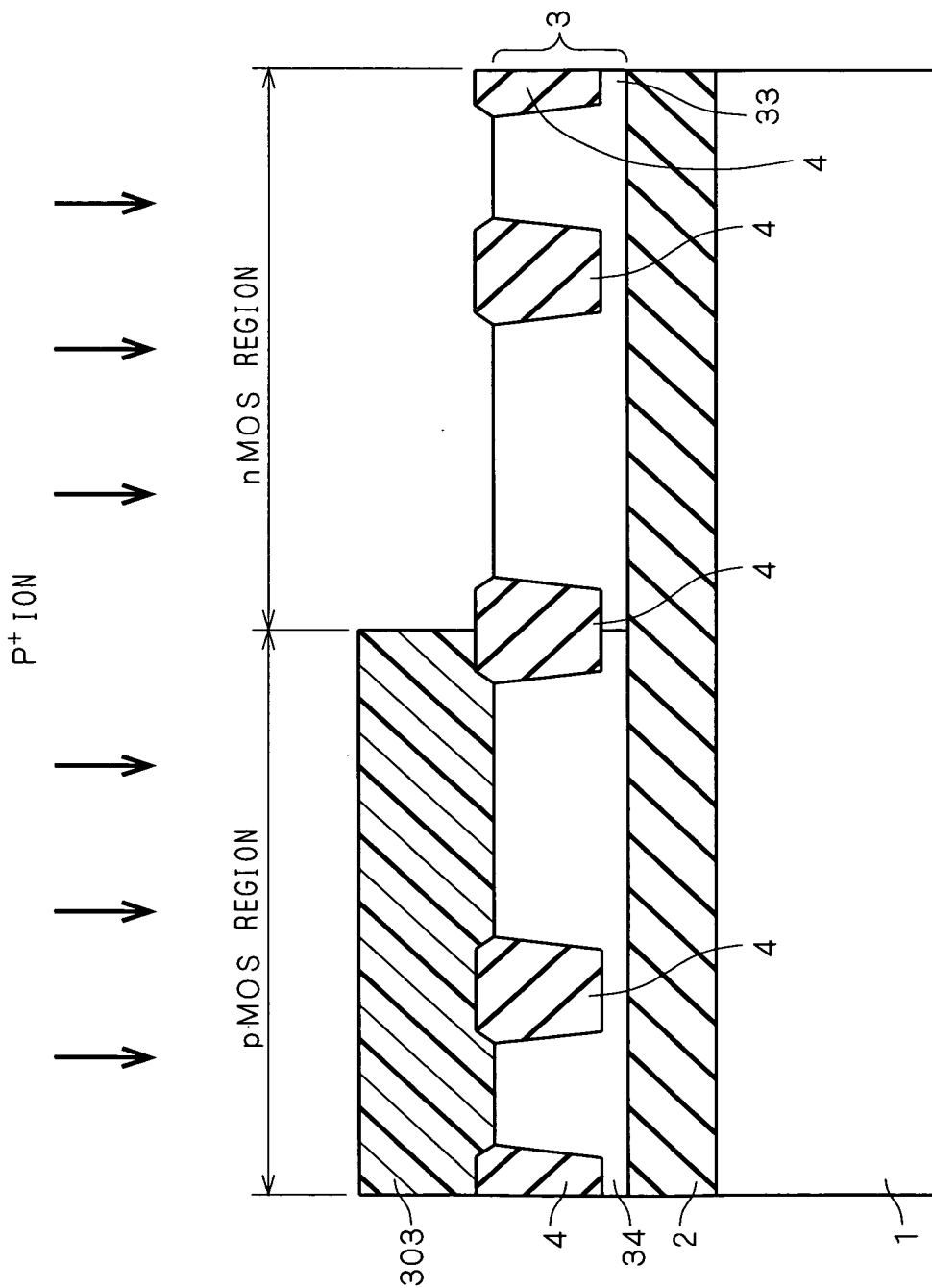


FIG. 16

FIG. 17

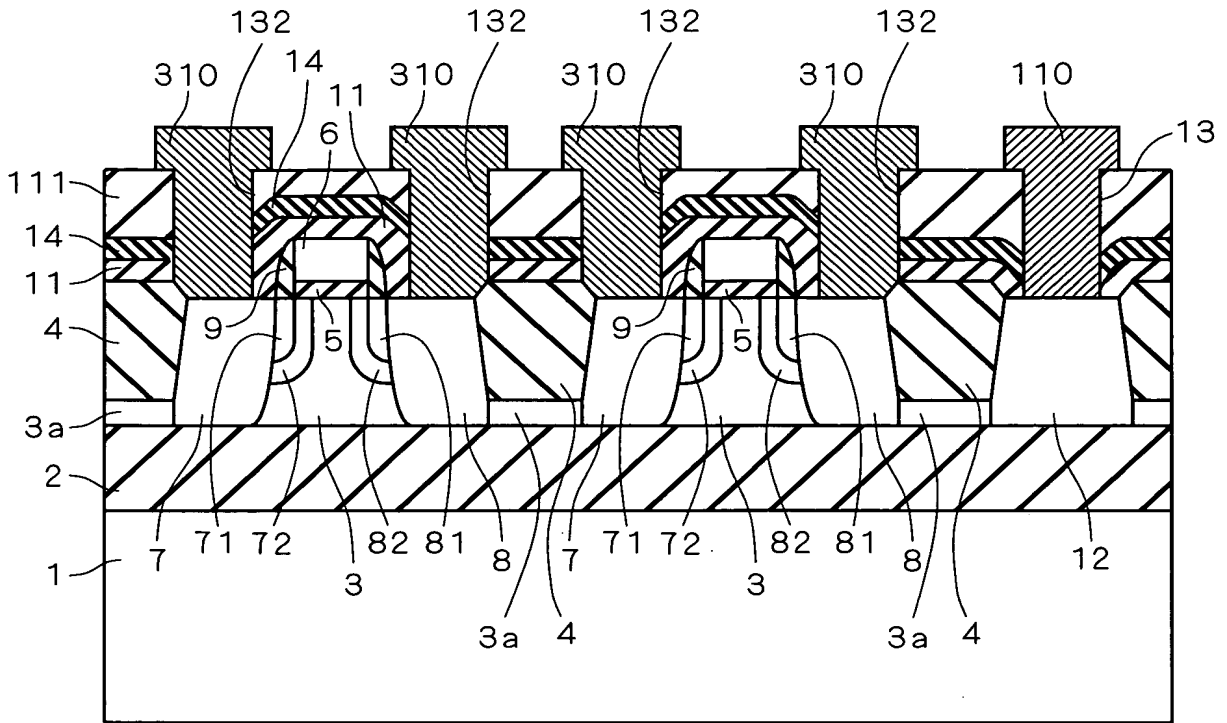
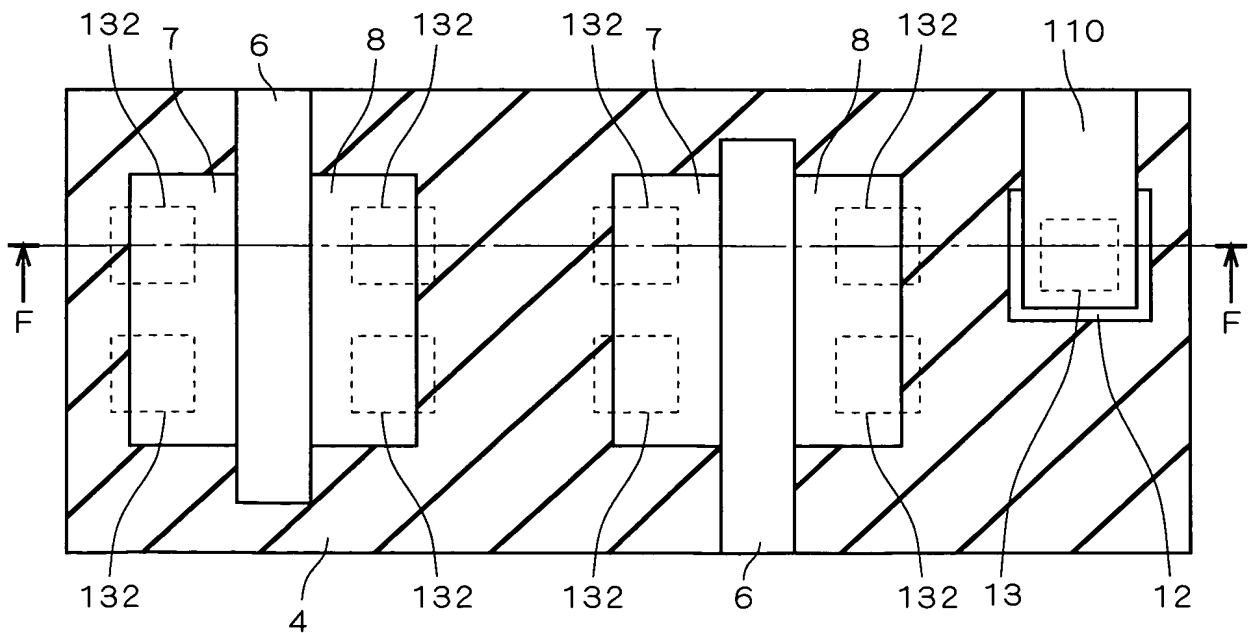


FIG. 18





This cross-sectional view shows a repeating array of semiconductor structures. A substrate (1) is at the base. Above it is a layer (2) with a pattern of rectangular regions (3) and (3a). On top of layer 2 are gate structures (4) with a central opening (5). The gate structures are separated by regions (7) and (71). Above the gates are pillars (6) with a central opening (9). The pillars are separated by regions (8) and (81). The top surface is covered by a layer (11) with a pattern of rectangular regions (111) and (14). The side walls of the pillars and gates are covered by a layer (12).

FIG. 23

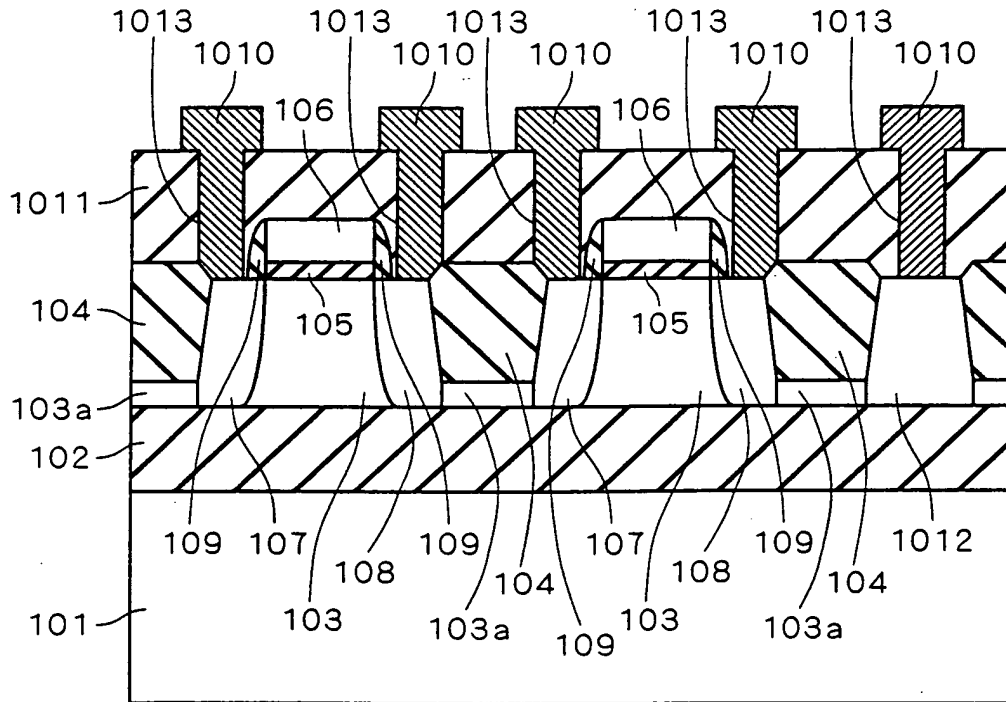


FIG. 24

